

SONY®

CX20185

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ReadWrite Amplifier for Floppy Disk Drive

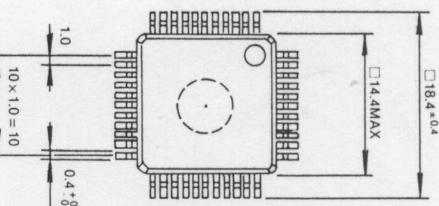
Functions:
CX20185 is an integrated circuit designed for ReadWrite of Floppy Disk Drive (FDD).
This IC offers the following features.

- Including Head Sw Matrix for selecting ReadWrite.
- The voltage gain of Pre-Amplifier can be selected to 100 or 200 by connecting the external capacitor.
- Peak Shift is less than 1% over Pre-Amplifier input range of 0.25 mV_{P-P} to 10 mV_{P-P} without adjustment.
- Time Domain Filter contains retriggerable monostable multivibrator which has internal timing capacitor allowing to be used only external resistor.
- Common, Write, and Erase drivers have large current capacities to satisfy versatile FDD's conditions.
- Write current can be determined by external resistors and is virtually independent against a change of temperature and power supply voltage.
- Write current may be selected to two different values by Digital input signal, if Write current compensation is required on inner tracks of the disk.
- WRITE GATE and ERASE GATE input timings can be set independently.
- Power Monitor circuit with Schmitt-Trigger function inhibits illegal writing against power supply voltage fluctuation including power ON/OFF transients.
- The number of external components is greatly reduced by this one-chip ReadWrite IC.

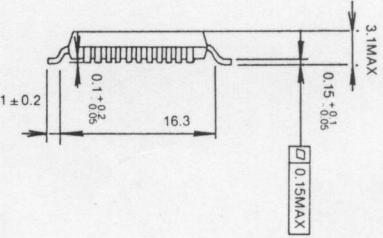
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

• Power Supply Voltage V_{CC2}	17V
• Power Supply Voltage V_{CC1}	7V
• Digital Signal Inputs (NOTE 1) Input Voltage	-0.5 ~ +5.5V
• POWER ON OUTPUT Voltage Applied	15V
• ERASE OUTPUT Voltage Applied	20V
• COMMON ϕ , COMMON 1, SOURCE Currents	150mA
• POWER ON OUTPUT SINK Current	20mA
• ERASE OUTPUT SINK Current	150mA
• HEAD ϕA and ϕB , HEAD 1A and 1B, Voltage Applied	23V
• Operating Ambient Temperature	$T_{op} - 20^\circ\text{C} \sim +75^\circ\text{C}$
• Operating Junction Temperature	$T_j - 150^\circ\text{C}$
• Storage Temperature	$T_{Stg} - 65^\circ\text{C} \sim +150^\circ\text{C}$

NOTE 1: These inputs are WRITE CURRENT, WRITE DATA, WRITE GATE, ERASE GATE, SIDE 1, and MMVA CONTROL



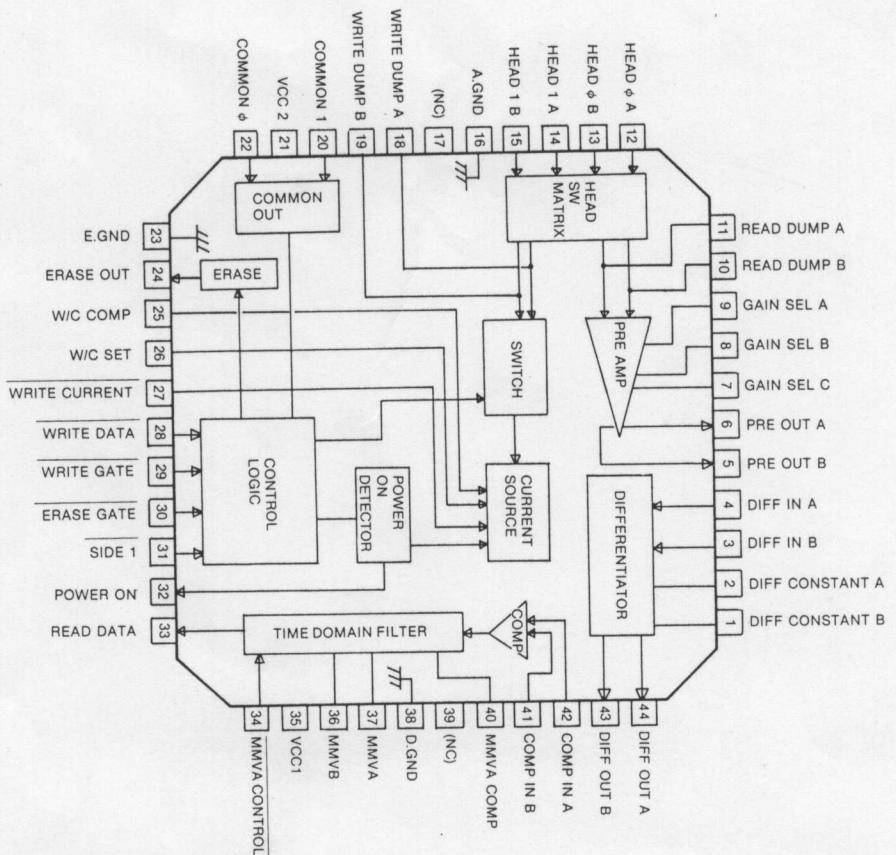
Package Outline (unit: mm)



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Block Diagram



Terminal Description	Function
HEAD _φ A HEAD _φ B COMMON _φ	Input and output terminals for Read/Write head on Side φ
HEAD1 A HEAD1 B COMMON1	Input and output terminals for Read/Write head on Side 1
READ DUMP A READ DUMP B	Connect the center tap of Read/Write head on Side 1
GAIN SEL A GAIN SEL B GAIN SEL C	Connect the center tap of Read/Write head on Side 1
PRE OUT A PRE OUT B	Connect the head dumping resistor for Read
DIFF IN A DIFF IN B	The voltage gain of Pre-Amplifier can be set to 100 or 200 by connecting a capacitor between these pins.
DIFF CONSTANT A DIFF CONSTANT B	Pre-Amplifier output
DIFF OUT A DIFF OUT B	Differentiator input
COMP IN A COMP IN B	Connect external components to set the differential constant.
COMP OUT A COMP OUT B	Differentiator output
COMP INN	Comparator input
MMVA COMP	Connect a resistor for the pulse width compensation of Time Domain Filter's mono-multi.
D GND	Digital circuit Ground
MMVA	Connect a resistor to determine the pulse width of Time Domain Filter's mono-multi.
MMVB	Connect a resistor to determine the pulse width of Read Data output.
VCC1	5V Power supply terminal
MMVA CONT	Digital input pin. When MMVA CONT is set to "L", the pulse width of Time Domain Filter's mono-multi is decreased.
READ DATA	Read Data output (Totem-Pole output)
POWER ON	Open Collector output. When Power Monitor circuit detects the power supply voltage drop, POWER ON output is ON.
SIDE 1	Digital input pin. When SIDE 1 is set to "L", Read/Write head on Side 1 becomes Active.
ERASE GATE	Digital input pin. When ERASE GATE is set to "L", Erase circuit becomes Active, causing Erase current to be ON.
WRITE GATE	Digital input pin. When WRITE GATE is set to "L", Write circuit block becomes Active, causing Write current to be ON.
WRITE DATA	Digital input pin with Schmitt-Trigger function. When WRITE DATA is set from "H" to "L", Write current is switched.
WRITE CURRENT	Digital input pin. When WRITE CURRENT is set to "L", Write current is increased.
W/C SET	Connect a resistor to determine Write current.
W/C COMP	Connect a resistor for Write current compensation.
ERASE OUT	Open Collector Erase current output.
E. GND	Erase circuit Ground
WRITE DUMP A WRITE DUMP B	Connect the head dumping resistor for Write.
VCC2	12V Power supply terminal
A. GND	Analog circuit Ground

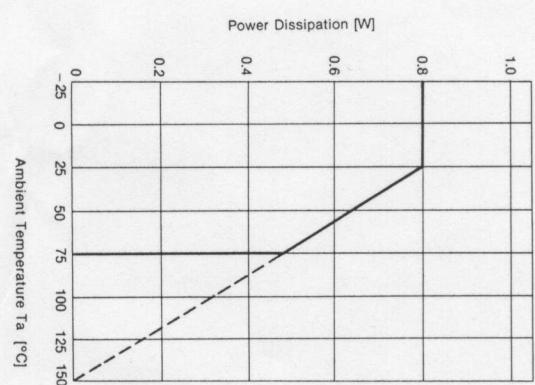
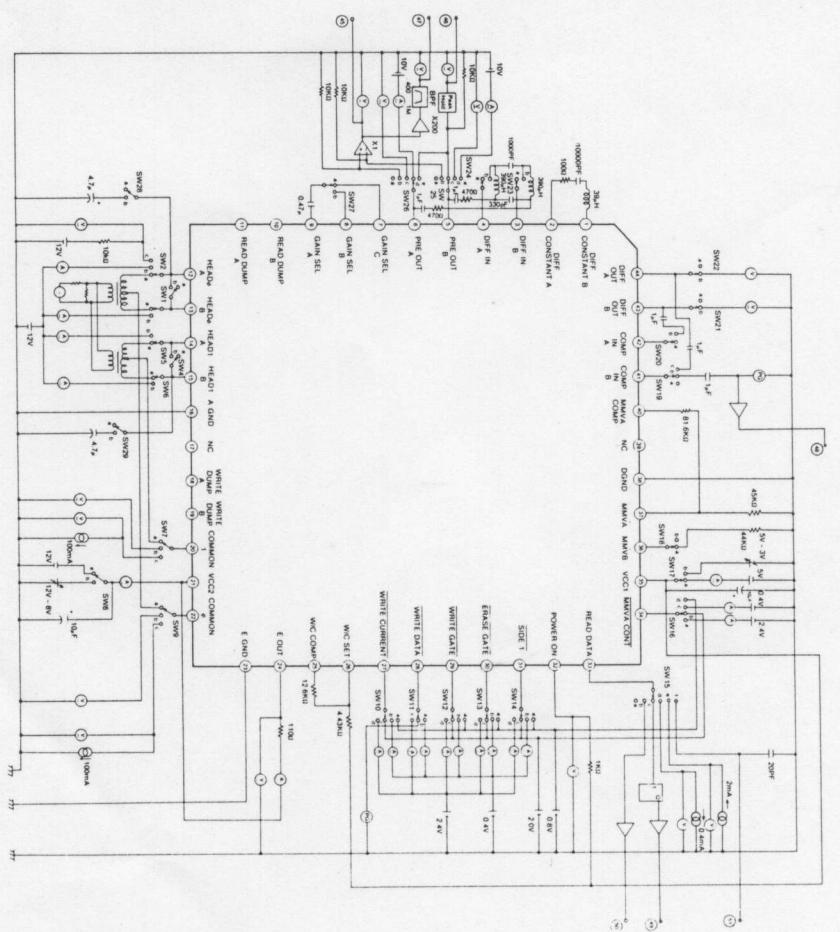
Electrical Characteristics
($V_{CC1} = 5V$, $V_{CC2} = 12V$, $T_a = 25^\circ C$ unless specified)

Characteristic	Symbol	Min	Typ	Max	Unit
Head Input Terminal Leakage Current (Write)	I LKM	—	—	10.0	μA
Head Selector/Pre-Amplifier Voltage Gain Accuracy	EGV	-15.0	—	+15.0	%
Head Selector/Pre-Amplifier High Frequency Gain Attenuation ($f = 5\text{ MHz}$)	BW	—	—	3.0	dB
Pre-Amplifier Differential Output Offset Voltage	V OFS	—	—	0.5	V
Pre-Amplifier Output Voltage Swing	V OUT	3.7	4.2	—	V P-P
Pre-Amplifier Differential Output Current Swing	I OUT	3.0	4.0	—	mA P-P
Pre-Amplifier Input Equivalent Noise Voltage (P_{Pe-Amp} Gain, >200 , $f = 400\text{Hz}$ to 1MHz)	EN	—	4.5	5.5	μV
Differentiator Differential Output Offset Voltage	V OFD	—	—	10.0	mV
Pulse Width Accuracy of Time Domain Filter's Mono-Multi	ETM1	-10.0	—	+10.0	%
Pulse Width Accuracy of Read Data Output	ETM2	-15.0	—	+15.0	%
Pulse Width Compensation Accuracy of Time Domain Filter's Mono-Multi	ETM1C	-15.0	—	+15.0	%
Peak Shift ($V_{IN} = 0.25 \sim 10\text{ mV}_{P-P}$)	PS	—	—	1.0	%
Write Current Accuracy	EW	-7.0	—	+7.0	%
Write Current Imbalance	DW	—	—	1.0	%
Write Current Compensation Accuracy	EWC	-10.0	—	+10.0	%
Head Input Terminal Saturation Voltage (Write)	V SAT	—	—	3.6	V
Common Voltage "L" (Write)	V WLCM	—	—	0.1	V
Common Voltage "H" (Write)	V WHCM	10.5	—	—	V
Common Voltage "H"	V RHOM	4.8	—	5.4	V
(Read)					
Erase Current Output Saturation Voltage	VIR	—	—	0.5	V
Erase Current Output Leakage Current	I LKIR	—	—	15.0	μA
Low-Level Input Voltage	V LIN	—	—	0.8	V
High-Level Input Voltage	V HIN	2.0	—	—	V
Low-Level Input Voltage (Terminal 28) (Schmitt Trigger Input)	V LINS	—	—	0.8	V
High-Level Input Voltage (Terminal 28) (Schmitt Trigger Input)	V HINS	2.0	—	—	V
Low-level Input Current	I LIN	—	—	250.0	μA

Characteristic	Symbol	Min	Typ	Max	Unit
High-Level Input Current (Terminals 28, 29, 30, and 31) (Terminal 27)	I HIN1	—	—	10.0	μA
High-Level Input Current (Terminal 34)	I HIN2	—	—	130.0	μA
Power ON/OFF Detector V_{CC1} Threshold Voltage	I HIN3	—	—	60.0	μA
Power ON/OFF Detector V_{CC2} Threshold Voltage	V TH5	3.6	4.0	4.4	V
Read Data Output Low-Level Output Voltage ($I_{OL} = 2\text{ mA}$)	V LOUT	—	—	0.5	V
Read Data Output High-Level Output Voltage ($I_{OH} = 0.4\text{ mA}$)	V HOUT	2.8	—	—	V
Read Data Output Rise Time	TR	—	—	100.0	nS
Read Data Output Fall Time	TF	—	—	100.0	nS
V_{CC1} Supply Current (Read)	I CC1R	16.0	22.0	28.0	mA
V_{CC1} Supply Current (Write)	I CC1W	7.0	12.5	16.5	mA
V_{CC2} Supply Current (Read)	I CC2R	7.0	10.0	14.0	mA
V_{CC2} Supply Current (Write)	I CC2W	9.0	12.5	16.0	mA

Derating Curve

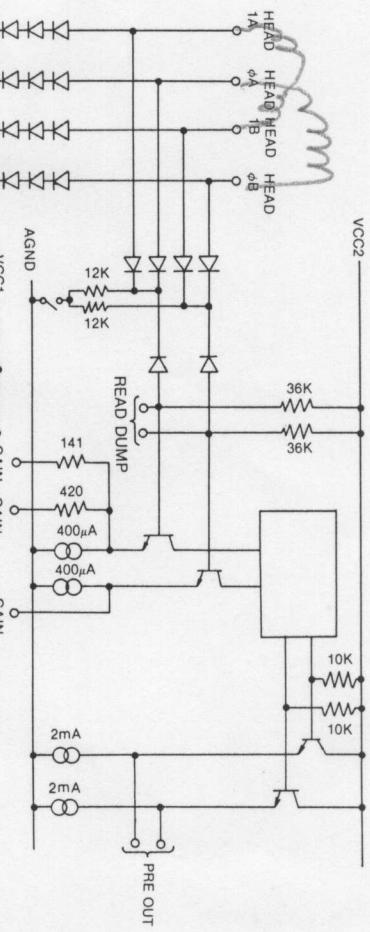
Electrical Characteristic Measuring Circuit



CX20185 INPUT/OUTPUT CIRCUIT

(2) DIFFERENTIATOR

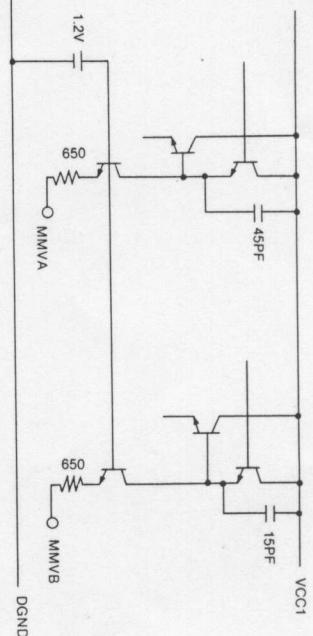
(1) PRE AMP



(3) COMPARATOR

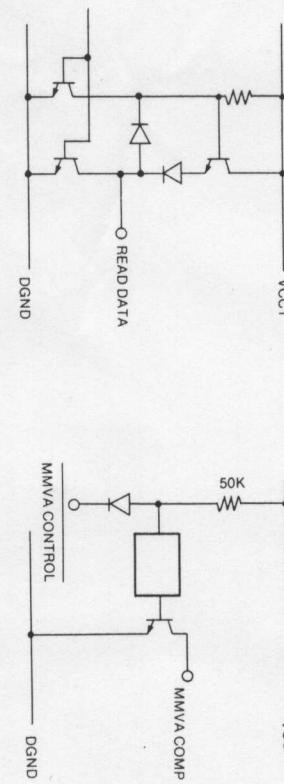


(4) TIME DOMAIN FILTER



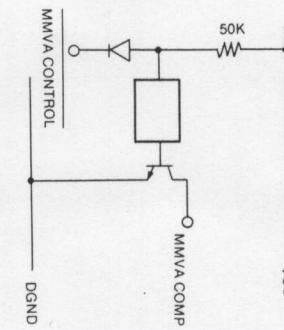
(5) READ OUTPUT

VCC1

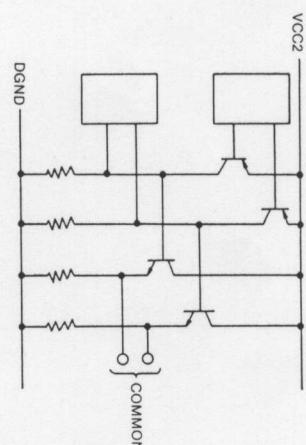


(6) MMVA CONTROL

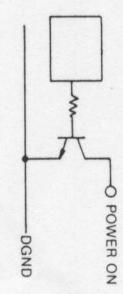
VCC1



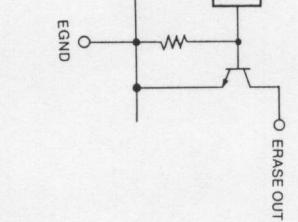
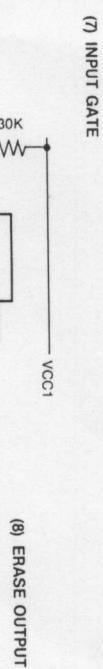
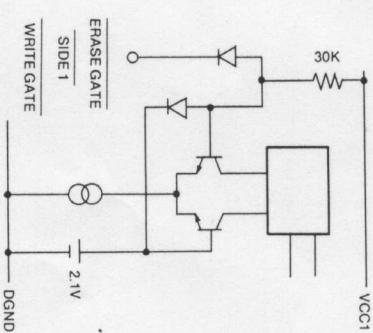
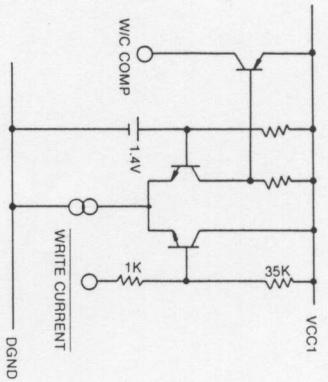
(10) COMMON



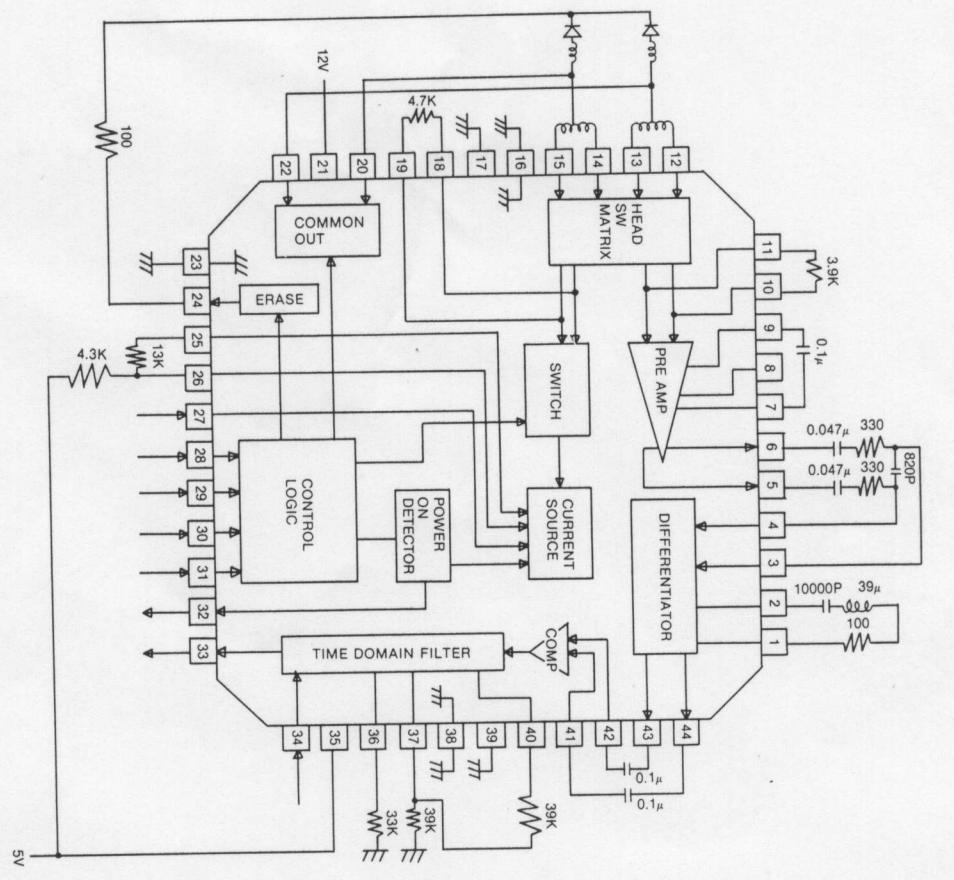
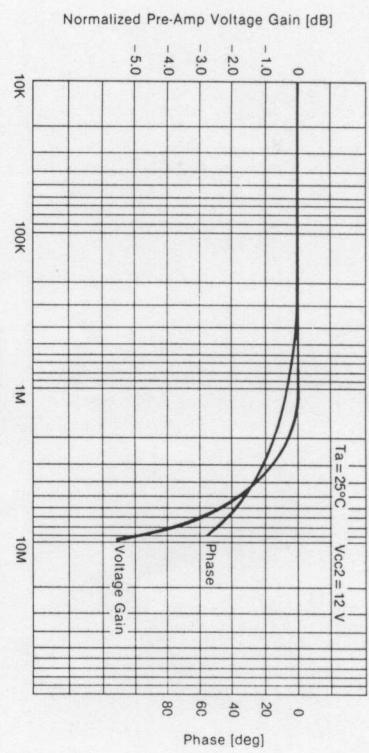
(11) POWER ON



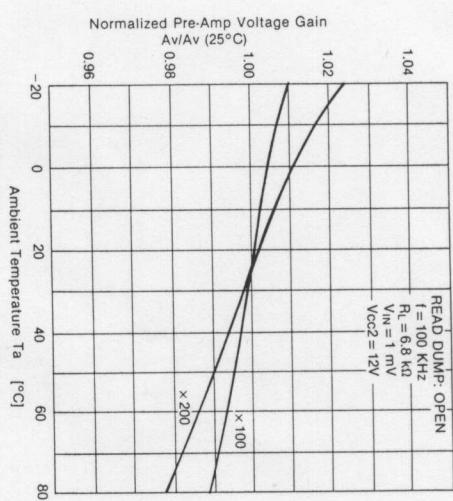
(9) W/C CONT



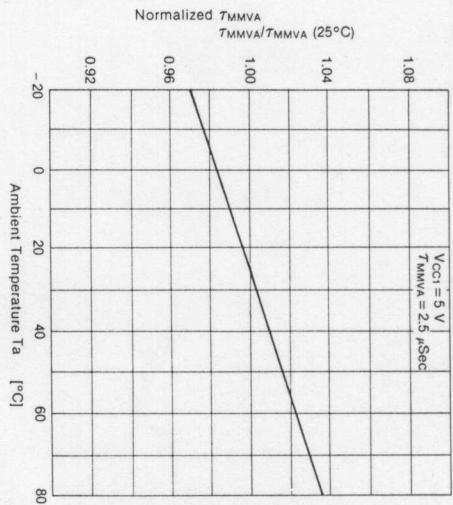
Example of Applied Circuit (For 300 rpm)

Phase and Normalized Voltage Gain
VS Frequency

Normalized Pre-Amp Voltage Gain
VS Temperature

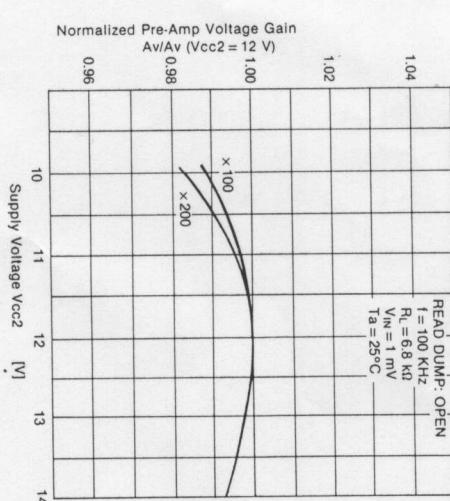


Normalized T_{MMVA} VS Temperature

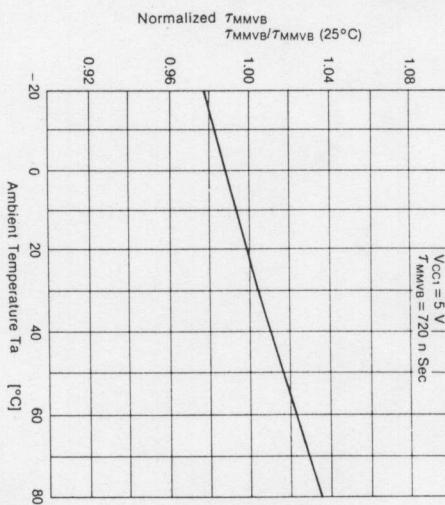


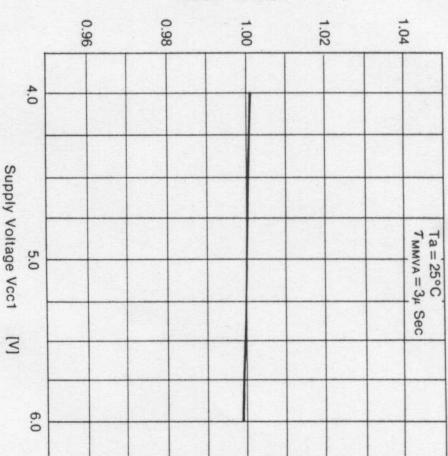
T_{MMVA} : Pulse Width of Time Domain Filter's Mono-Multi
 T_{MMVB} : Pulse Width of Read Data Output

Normalized Pre-Amp Voltage Gain VS V_{CC2}

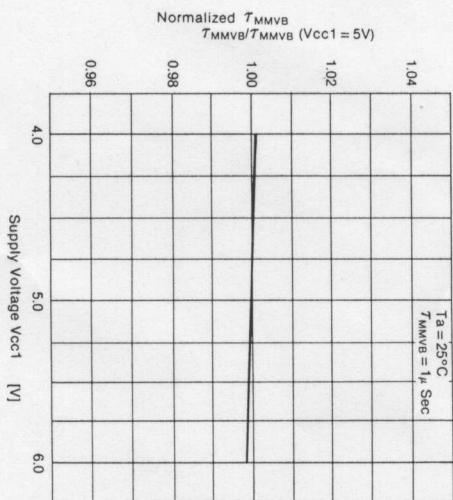
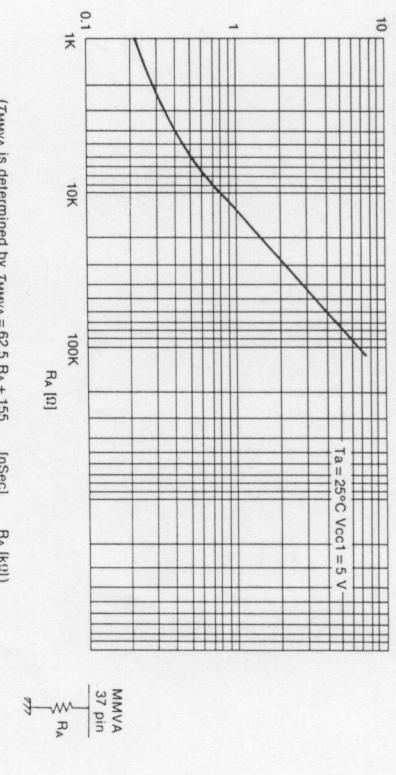


Normalized T_{MMVB} VS Temperature

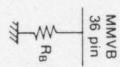
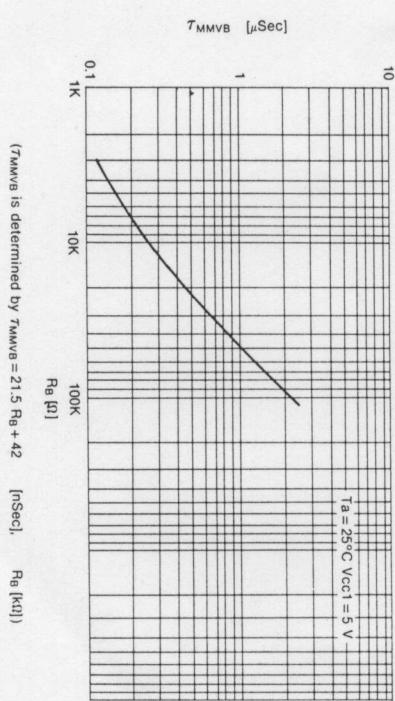


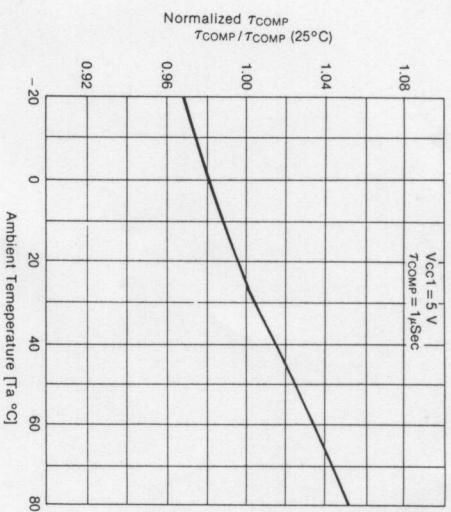
Normalized T_{MMVA} VS Vcc1

T_{MMVA} : Pulse Width of Time Domain Filter's Mono-Multi
 T_{MMVB} : Pulse Width of Read Data Output

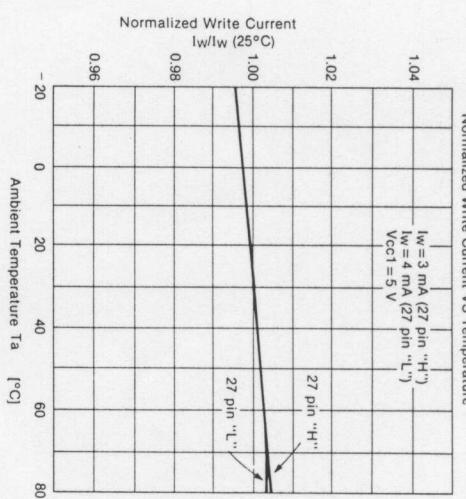
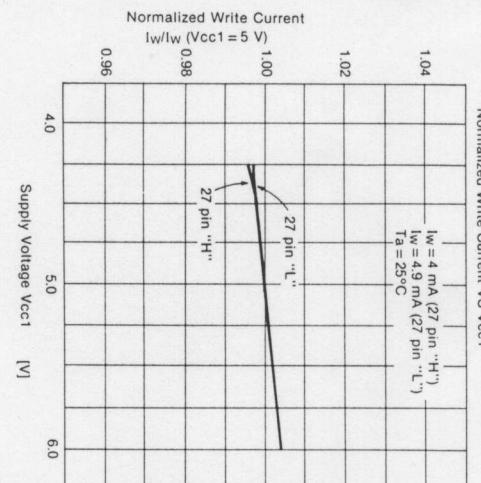
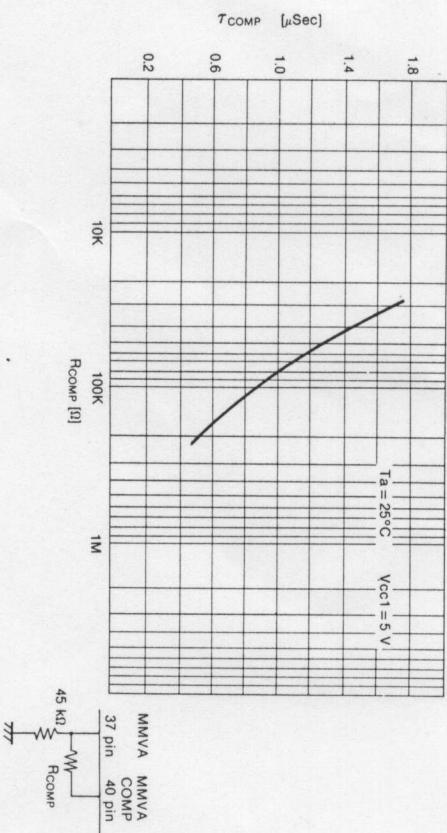
Normalized T_{MMVB} VS Vcc1 T_{MMVA} [μSec]

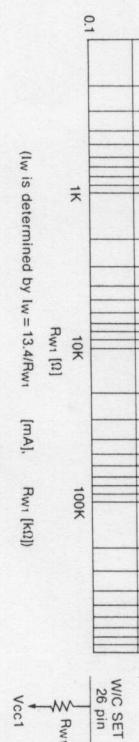
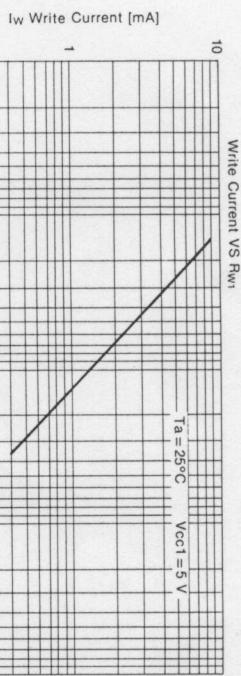
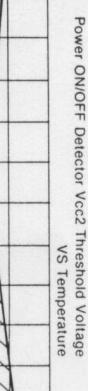
TMMVB VS RB



Normalized τ_{COMP} VS Temperature

τ_{COMP} : Pulse Width Compensation of Time Domain Filter's Mono-Multi
 $\tau_{COMP} = \tau_{MMVA}$ (34 pin "H") - τ_{MMVA} (34 pin "L")

 τ_{COMP} VS R_{COMP} 

Write Current VS R_{W1} Power ON/OFF Detector V_{cc1} Threshold Voltage [V]